

## **In the Claims**

Claims 1-38 (canceled).

Claim 39 (new): A method of forming a semiconductor construction, comprising:

- providing a semiconductor substrate;
- forming a first layer comprising silicon and nitrogen over the substrate;
- forming a second layer comprising carbon-hydrogen bonds over and physically against the first layer;
- forming a photoresist system over the second layer;
- exposing the photoresist system to patterned light and subsequently heating the photoresist system; the second layer releasing acid into the photoresist system during the heating; and
- after the heating, exposing the photoresist system to a developing solvent.

Claim 40 (new): The method of claim 39 wherein the second layer comprises at least 50 weight% carbon.

Claim 41 (new): The method of claim 39 wherein the first layer comprises silicon, oxygen and nitrogen.

Claim 42 (new): The method of claim 39 wherein the first layer consists essentially of silicon oxynitride.

Claim 43 (new): The method of claim 39 wherein the forming the second layer comprises spin-coating the second layer across the first layer.

Claim 44 (new): The method of claim 39 wherein the second layer comprises a surfactant.

Claim 45 (new): The method of claim 39 wherein the second layer comprises a polymer.

Claim 46 (new): The method of claim 39 wherein the second layer comprises a cross-linked polymer.

Claim 47 (new): The method of claim 39 wherein the second layer comprises an acrylic polymer.

Claim 48 (new): The method of claim 39 wherein the second layer comprises a component that absorbs light having a wavelength within a region from 150 nanometers to 250 nanometers.

Claim 49 (new): A method of forming a semiconductor construction, comprising:

providing a semiconductor substrate comprising monocrystalline silicon;

forming a first layer comprising silicon and nitrogen over the substrate;

forming a second layer comprising at least 50 weight% carbon over the first layer;

forming a photoresist system over the second layer;

• exposing a first portion of the photoresist system to radiation while not exposing a second portion to the radiation;

subjecting the photoresist system to conditions which cause either the exposed first portion or unexposed second portion of the photoresist system to release acid; the second layer also releasing acid as the photoresist system is exposed to the conditions; and

after subjecting the photoresist system to the conditions, removing either the first or second portion selectively relative to the other of the first and second portion.

Claim 50 (new): The method of claim 49 wherein the conditions which cause either the exposed first portion or unexposed second portion of the photoresist system to release acid comprise heating of the photoresist system to a temperature of at least about 90°C.

Claim 51 (new): The method of claim 49 wherein the first layer comprises silicon, oxygen and nitrogen.

Claim 52 (new): The method of claim 49 wherein the first layer consists essentially of silicon oxynitride.

Claim 53 (new): The method of claim 49 wherein the forming the second layer comprises spin-coating the second layer across the first layer.

Claim 54 (new): The method of claim 49 wherein the second layer comprises a surfactant.

Claim 55 (new): The method of claim 49 wherein the second layer comprises a polymer.

Claim 56 (new): The method of claim 49 wherein the second layer comprises a cross-linked polymer.

Claim 57 (new): The method of claim 49 wherein the second layer comprises an acrylic polymer.

Claim 58 (new): The method of claim 49 wherein the second layer comprises a component that absorbs light having a wavelength within a region from 150 nanometers to 250 nanometers.